

5 é / Descriptions

9 5 : .> // x 4 6 4 !- } â 'ož Silicon NPN transistor in a SOT-23 Plastic Package.

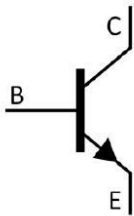
α^a / Features

2 3 ; mož
Complementary pair with L8550M.

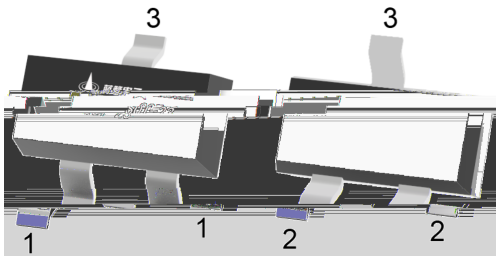
Đ ÷ / Applications

9 ä y Ý èož
Power amplifier applications.

Ã W] Ô . / Equivalent Circuit



• Ů - æ / Pinning



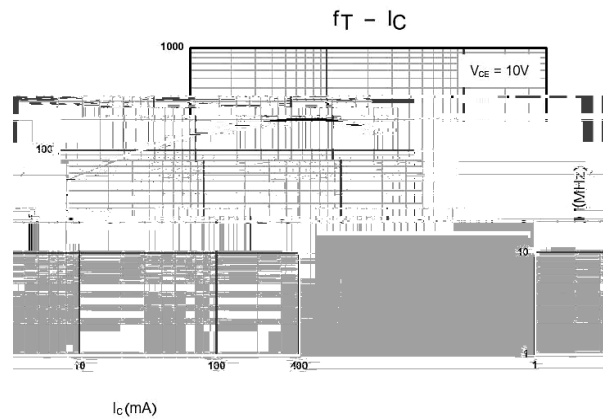
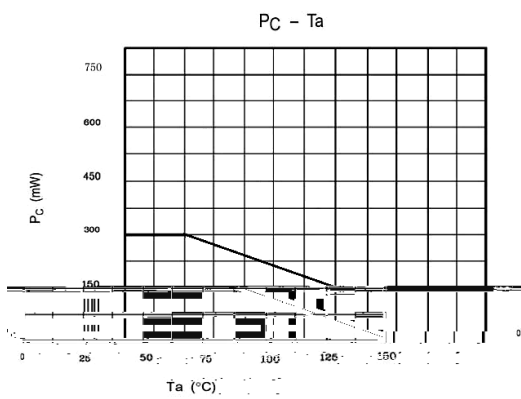
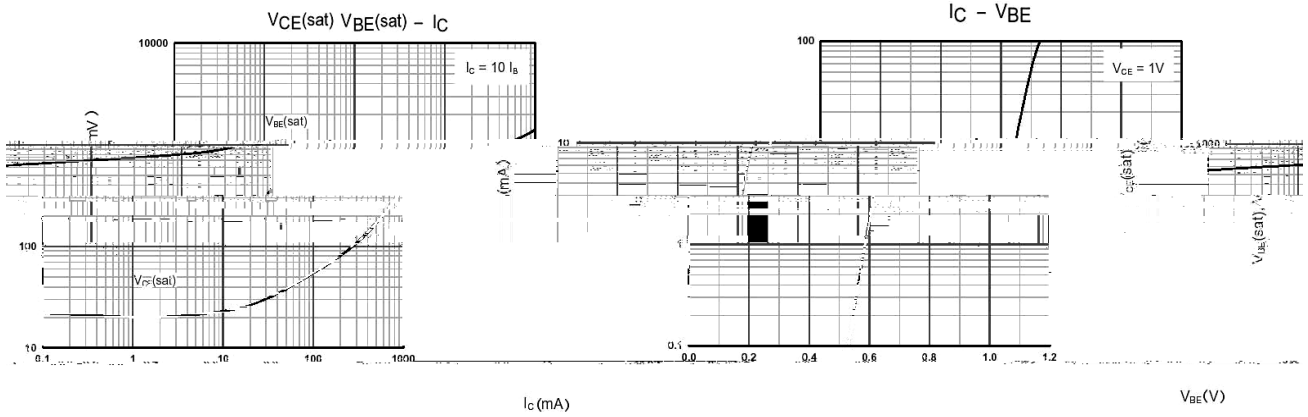
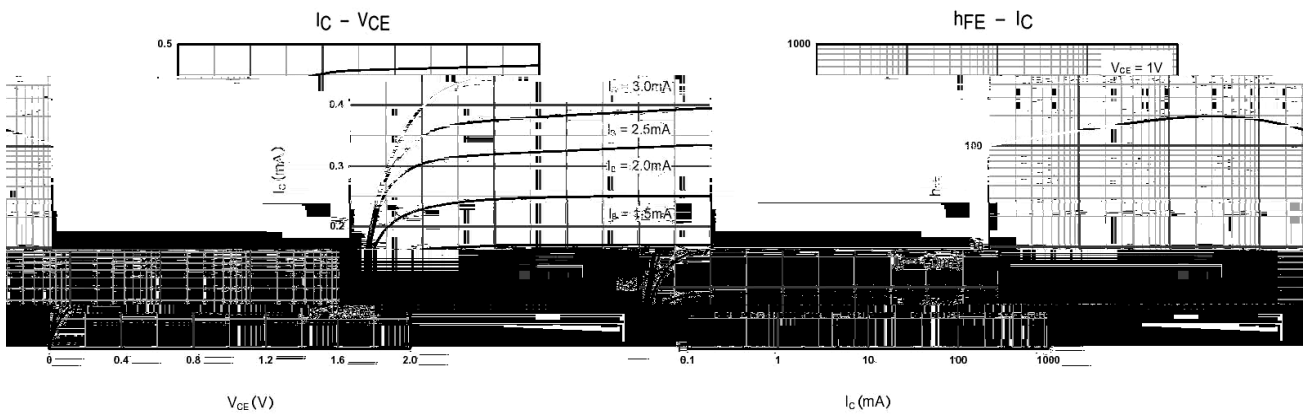
PIN1 y Base PIN 2 y Emitter PIN 3 y Collector

Z Ü B , M V / h_{FE} Classifications & Marking

h _{FE} Classifications Symbol	B	C	D
h _{FE} Range	85 160	120 200	160 300
Marking	HY1B	HY1C	HY1D

@ f Parameter	... Z Symbol	f › Rating	% y Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	1.5	A
Base Current	I_B	0.5	A
Collector Power Dissipation	P_C	300	mW

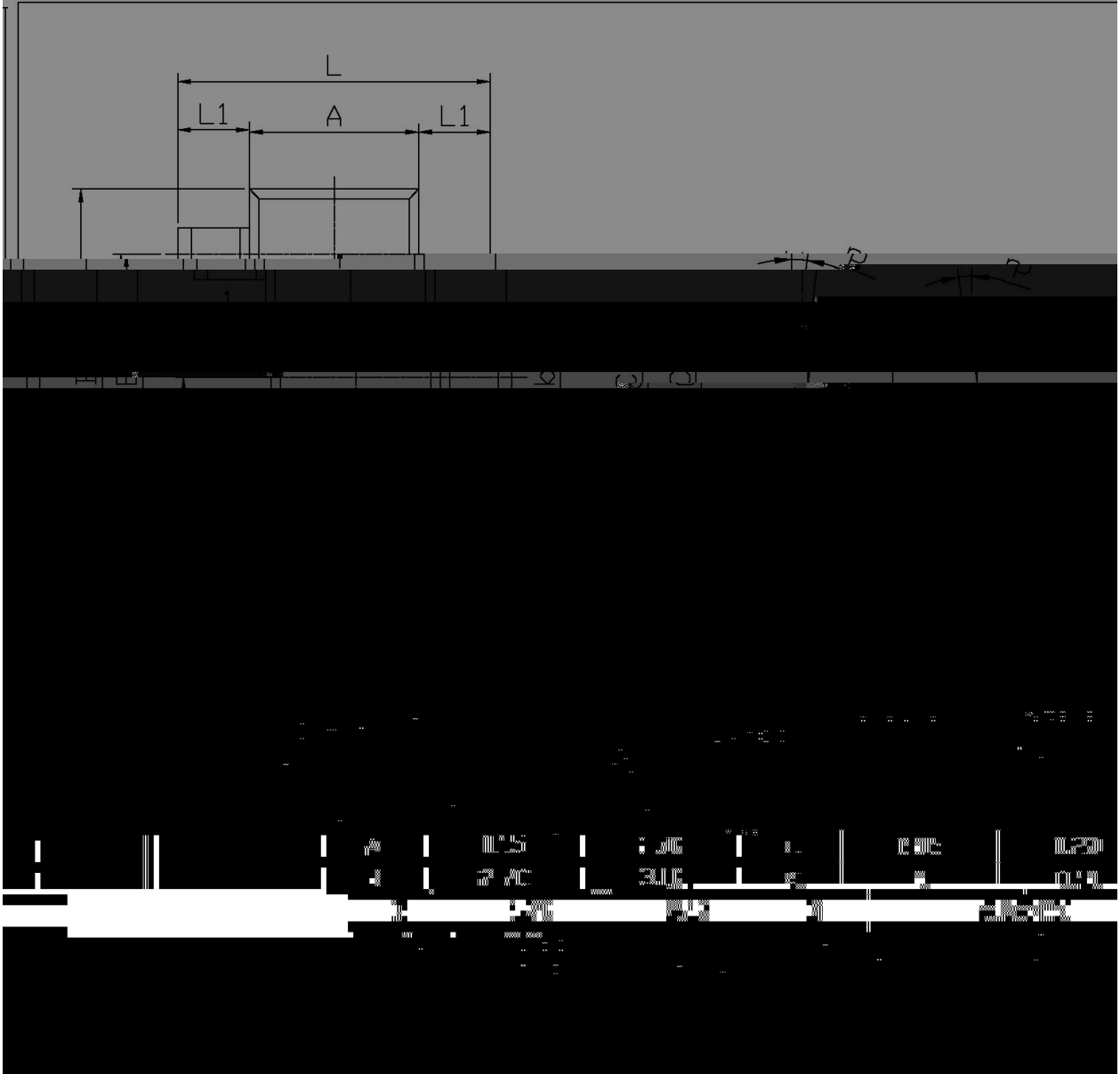
Electrical Characteristic Curve



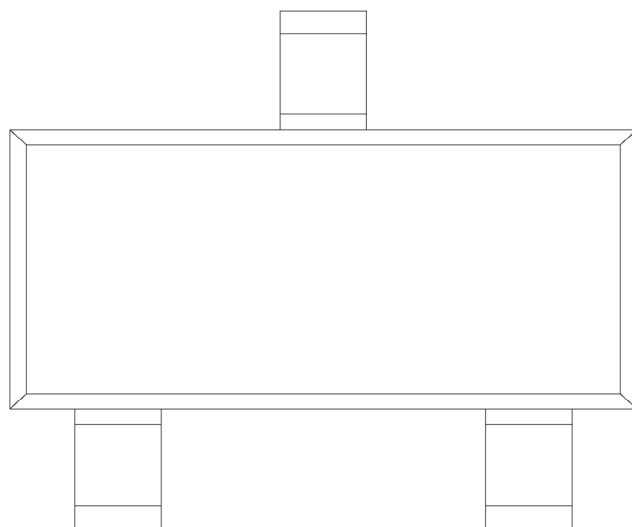
Ø □ =) φ / Package Dimensions

SMT-23

单位: mm



, M y f / Marking Instructions



^a ϕ y

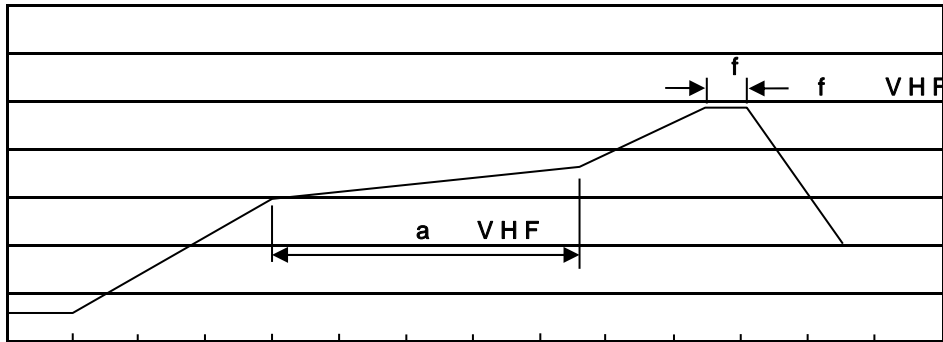
. y , [W A

? y ° Z W A

(y N -ž Ä •te p" v0 Đ vt XI %;rÄGpGUp" %oĐ AW ="GP(N %oŕŕpwWϕ y N

šWD t... • Žč (x/) / :KSVKXGZ[XK 6XULORK LUX /8 8KLRU] 9URJKXOTM 6

7HP SHUDW XUH



7LPH VHF

a č y

1o• Ä ½ “ † 150 ½180 - k ž • 60 ½90sec;

2o• Q › “ † 245 r5 - k ž • 4 Ö 5 r0.5sec;

3o•D N ò i Ò 0 , † 2 ½10 - /sec.

Note:

1.Preheating:150~180 - , Time:60~90sec.

2.Peak Temp.:245 r5 - , Duration:5 r0.5sec.

3. Cooling Speed: 2~10 - /sec.

ÂD /Cã p ~ »] / Resistance to Soldering Heat Test Conditions

“ † y 260 r5 -

ž • y 10 r1 sec.

Temp.:260 r5 -

Time:10 r1 sec

G P á / Packaging SPEC.

2 & x / REEL

Package Type 7>û ~ E	Units ;>û !H					Dimension ;>û p . (unit /mm³)		
	Units/Reel / --	Reels/Inner Box -- /-	Units/Inner Box /-	Inner Boxes/Outer Box - /1ç	Units/Outer Box /1ç	Reel	Inner Box	Outer Boxç
SOT-23	3,000	10	30,000	6	180,000	7 s x8	180x120x180	390x385x205

„ ð y f / Notices